FOREWORD

Dielectric Thin Films for Future Electron Devices: Science and Technology

To cite this article: 2014 Jpn. J. Appl. Phys. 53 08L001

View the article online for updates and enhancements.
FOREWORD

Dielectric Thin Films for Future Electron Devices: Science and Technology

This special issue contains a selection of papers presented at the 2013 International Workshop on “Dielectric Thin Films for Future Electron Devices: Science and Technology” (IWDTF2013) held at University of Tsukuba (Tokyo campus) in Tokyo, Japan from November 7th to 9th in 2013. IWDTF2013 was sponsored by the Japan Society of Applied Physics (JSAP). The purpose of the workshop was to exchange information and ideas regarding reliability, variability, characterization, process technologies and related physical phenomena for the next generation logic, memory, power, analog, and sensor and the display devices. 140 scientist and engineers attended the workshop, and 73 papers were presented in 10 oral and 1 poster sessions, including 2 keynote speeches and 8 invited talks. 18 papers had been accepted for publication in this special issue of the Japanese Journal of Applied Physics, Vol. 53, No. 8 (2014). The acceptance was made by referees according to the publication standards of the Japanese Journal of Applied Physics.

We sincerely hope that researchers developing future electron devices will find interesting knowledge in this special issue of IWDTF2013.

June, 2014

Hiroyuki Kageshima
Chairperson, Program Committee of IWDTF 2013

Shinichi Takagi
Vice Chairperson, Program Committee of IWDTF 2013

Renichi Yamada
Vice Chairperson, Program Committee of IWDTF 2013

CHIEF GUEST EDITOR

Shinichi Takagi (The University of Tokyo)

GUEST EDITORS

Hiroyuki Kageshima (Shimane University)
Koji Eriguchi (Kyoto University)
Hidetoshi Nabatame (National Institute for Materials Science)
Osamu Nakatsuka (Nagoya University)
Takuji Hosoi (Osaka University)
Noriyuki Taoka (Nagoya University)